IN THE CLAIMS:

Please amend Claim 1, as follows:

1. (Once Amended) [thing] A thin film transistor comprising:

an insulator substrate;

a gate electrode located on the insulator substrate;

a gate insulator film provided above the insulator substrate [an] and the gate electrode; and

a polycrystalline silicon film located on the gate insulator film, the polycrystalline silicon film being formed by irradiating a laser beam on a surface of an amorphous silicon film to heat the amorphous silicon film,

the gate electrode having a center portion with a flat surface and a pair of tapered end portions with inclined surfaces, an angle between each of the inclined surfaces of the pair of tapered end portions and a surface of the insulator substrate being set within a range of 5° to 40° so that a uniform grain size of the polycrystalline silicon film is acquired above the center portion and the pair of tapered end portions, a gate withstand voltage of the thin film transistor, and the inclined surfaces of the pair of tapered end portions are prevented from increasing, wherein the laser beam is scanned on the surface of the amorphous silicon film such that a first portion of the amorphous silicon film above the gate electrode receives greater crystallization laser energy than a second portion of the amorphous silicon film above the insulator substrate, and a third portion of the amorphous silicon film above the center portion receives greater crystallization laser energy than fourth portions of the amorphous silicon film above tapered end portions.